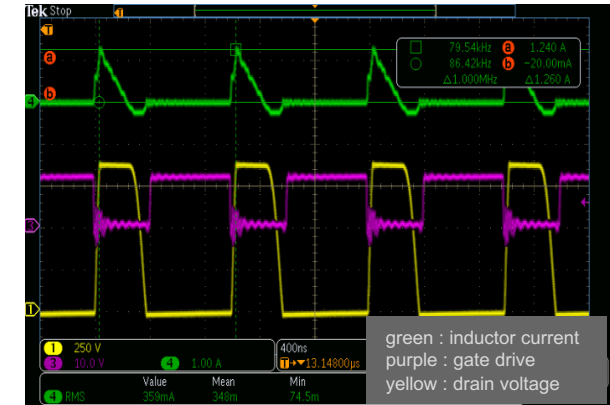
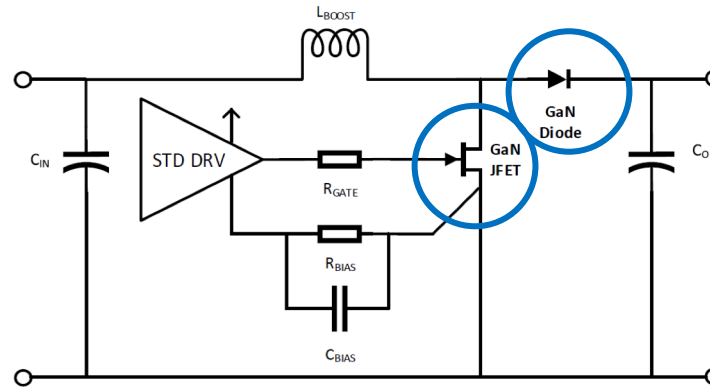


1 MHz ZVS Boost 200V to 800V, 100W



Unique Features

- Industry leading 1MHz switching frequency
- Very low switching losses enabled by NexGen Vertical GaN™ Components
- Vertical GaN™ Power eJFET 1200V Breakdown Voltage
- Vertical GaN™ Diode 1200V Breakdown Voltage
- Switching frequency increase to > 5MHz with air core inductor
- Very compact design with 70 x 47 mm² board dimensions

- Standard Silicon controller and MOSFET driver
- Except for NexGen GaN devices only standard components required

Key Performance Data

- ZVS CrCM Switching
- Efficiency >96% at 1MHz